



(FW)

Attorney's Docket No.: P16015C

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re Patent Application of:	)	
	)	
Justin K. Brask et al.	)	Examiner: Unassigned
	)	
Application No.: 10/748,090	)	Art Unit: Unassigned
	)	
Filed: December 29, 2003	)	
	)	
For: METHOD FOR MAKING A	)	
SEMICONDUCTOR DEVICE HAVING A	)	
<u>HIGH-K GATE DIELECTRIC</u>	)	

Commissioner for Patents  
P.O. Box 1450  
Alexandria, Virginia 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

Enclosed is a copy of Information Disclosure Citation Form PTO-1449 or PTO/SB/08 together with copies of the documents cited on that form, except for copies not required to be submitted (e.g., copies of U.S. patents and U.S. published patent applications need not be enclosed for applications filed after June 30, 2003). It is respectfully requested that the cited documents be considered and that the enclosed copy of Information Disclosure Citation Form PTO-1449 or PTO/SB/08 be initialed by the Examiner to indicate such consideration and a copy thereof returned to applicant(s).

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail with sufficient postage in an envelope addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, Virginia 22313-1450 on August 17, 2004.  
(Date of Deposit)

Teresa Mattox

(Typed or printed name of person mailing correspondence)

Teresa Mattox

(Signature of person mailing correspondence)

Pursuant to 37 C.F.R. § 1.97, the submission of this Information Disclosure Statement is not to be construed as a representation that a search has been made and is not to be construed as an admission that the information cited in this statement is material to patentability.

Pursuant to 37 C.F.R. § 1.97, this Information Disclosure Statement is being submitted under one of the following (as indicated by an "X" to the left of the appropriate paragraph):

X 37 C.F.R. §1.97(b).

37 C.F.R. §1.97(c). If so, then enclosed with this Information Disclosure Statement is one of the following:

A statement pursuant to 37 C.F.R. §1.97(e) or

A check for \$180.00 for the fee under 37 C.F.R. § 1.17(p).

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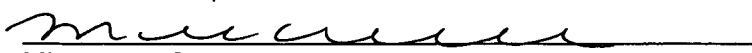
- (1) A statement pursuant to 37 C.F.R. §1.97(e); and
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If there are any additional charges, please charge Deposit Account No. 02-2666.

Respectfully submitted,

BLAKELY, SOKOLOFF, TAYLOR & ZAFMAN LLP

Dated: 8/17, 2004

  
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## STATEMENT BY APPLICANT

*(use as many sheets as necessary)*

Sheet 1 of 2

Application Number	10/748,090
Filing Date	December 29, 2003
First Named Inventor:	Justin K. Brask et al.
Art Unit	Unknown
Examiner Name	Unknown
Attorney Docket Number	P16015C

[illegible]

Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Country Code <sup>3</sup> Number <sup>4</sup> Kind Code <sup>5</sup> (if known)				
		EP 0 641 027 A	10/5/1999	Ohmi Tadahiro		

Examiner  
Signature

Date Considered

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<b>Substitute for Form 1449/PTO</b>  <b>INFORMATION DISCLOSURE</b> <b>STATEMENT BY APPLICANT</b> <i>(use as many sheets as necessary)</i>			<b>Complete if Known</b>		
			Application Number	10/748,090	
			Filing Date	December 29, 2003	
			First Named Inventor:	Justin K. Brask et al.	
			Art Unit	Unknown	
			Examiner Name	Unknown	
<b>Sheet</b>	2	<b>of</b>	2	Attorney Docket Number	P16015C

**NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T <sup>2</sup>
		Chih-Wei, Yang et al, "Dramatic Reduction of Gate Leakage Current in 1.61nm HfO2 High-K Dielectric Poly-silicon Gate with A1203 Capping Layers", Electronics Letters, Vol. 38, NO. 20, September 2002, pages 1223-1225, XP002288765	
		Osten, H.J. et al., "Epitaxial, High-K Dielectrics on Silicon: The Example of Praseodymium Oxide", Microelectronics and Reliability, Elsevier Science Ltd, GB, Vol. 41, 2001, pages 991-994 XP002265638	
		PCT International Search Report PCT/US 03/40688	

Examiner Signature		Date Considered	
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